

# FDMS8670AS

## N-Channel PowerTrench® SyncFET™

### 30V, 42A, 3.0mΩ

#### Features

- Max  $r_{DS(on)}$  = 3.0mΩ at  $V_{GS} = 10V, I_D = 23A$
- Max  $r_{DS(on)}$  = 4.7mΩ at  $V_{GS} = 4.5V, I_D = 18A$
- Advanced Package and Silicon combination for low  $r_{DS(on)}$  and high efficiency
- SyncFET Schottky Body Diode
- MSL1 robust package design
- RoHS Compliant

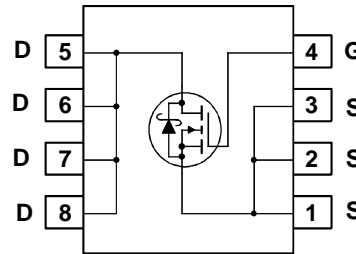
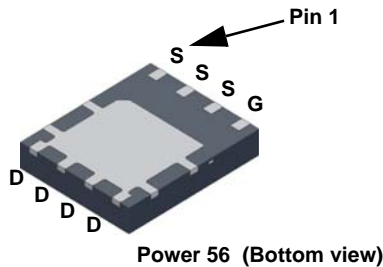


#### General Description

The FDMS8670AS has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest  $r_{DS(on)}$  while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.

#### Applications

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU low side switch
- Networking Point of Load low side switch
- Telecom secondary side rectification



#### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	42	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	127	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	23	
	-Pulsed	200	
$E_{AS}$	Single Pulse Avalanche Energy	384	mJ
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	50	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8670AS	FDMS8670AS	Power 56	13"	12mm	3000units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{mA}$ , referenced to $25^\circ\text{C}$		28		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			500	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 10\text{mA}$ , referenced to $25^\circ\text{C}$		-5		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 23\text{A}$		2.4	3.0	m $\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 18\text{A}$		3.5	4.7	
		$V_{GS} = 10\text{V}, I_D = 23\text{A}, T_J = 125^\circ\text{C}$		3.5	4.7	
$g_{FS}$	Forward Transconductance	$V_{DD} = 10\text{V}, I_D = 23\text{A}$		143		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		2718	3615	pF
$C_{oss}$	Output Capacitance			1537	2045	pF
$C_{riss}$	Reverse Transfer Capacitance			343	515	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		0.9		$\Omega$

### Switching Characteristics

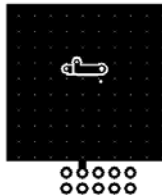
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}, I_D = 23\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$		14	26	ns	
$t_r$	Rise Time			5	10	ns	
$t_{d(off)}$	Turn-Off Delay Time			32	52	ns	
$t_f$	Fall Time			4	10	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{V}$ to $10\text{V}$		39	55	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V}$ to $4.5\text{V}$	$V_{DD} = 15\text{V}, I_D = 23\text{A}$		20	28	nC
$Q_{gs}$	Gate to Source Charge				7.2		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				4.0		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 2\text{A}$ (Note 3)		0.4	0.7	V
$t_{rr}$	Reverse Recovery Time	$I_F = 23\text{A}, di/dt = 300\text{A}/\mu\text{s}$		39	63	ns
$Q_{rr}$	Reverse Recovery Charge			48	77	nC

#### NOTES:

- $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper.



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

- Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 16\text{A}$ ,  $V_{DD} = 30\text{V}$ ,  $V_{GS} = 10\text{V}$ .

- Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

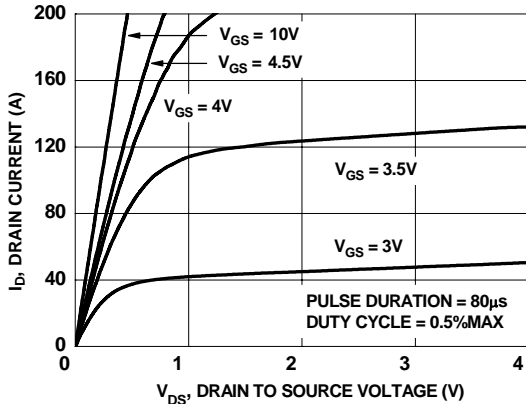


Figure 1. On-Region Characteristics

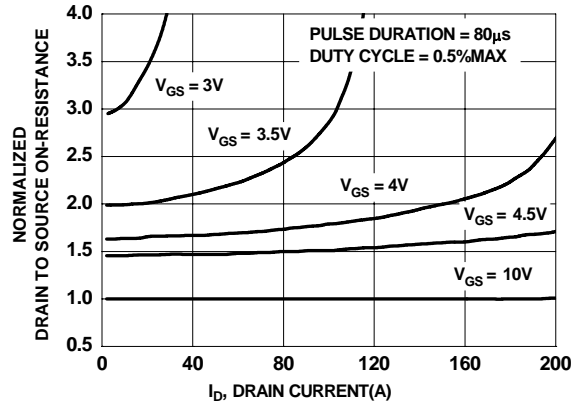


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

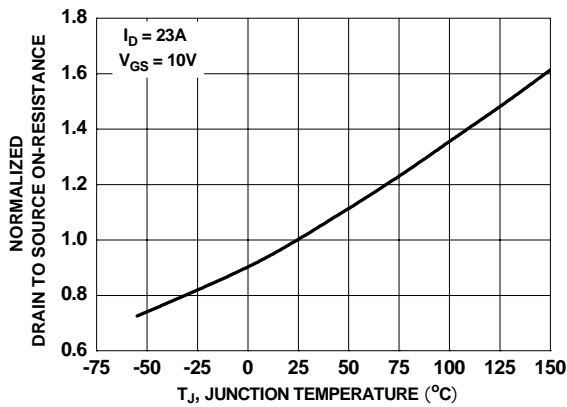


Figure 3. Normalized On-Resistance vs Junction Temperature

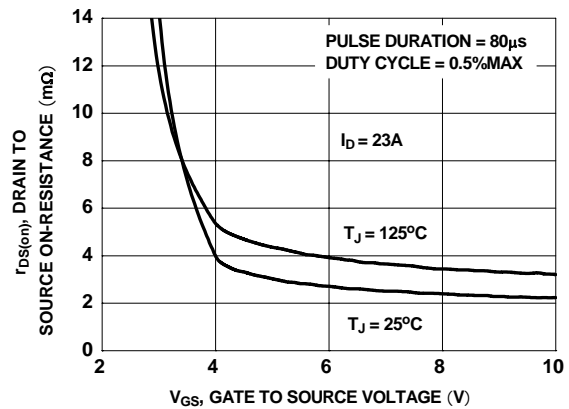


Figure 4. On-Resistance vs Gate to Source Voltage

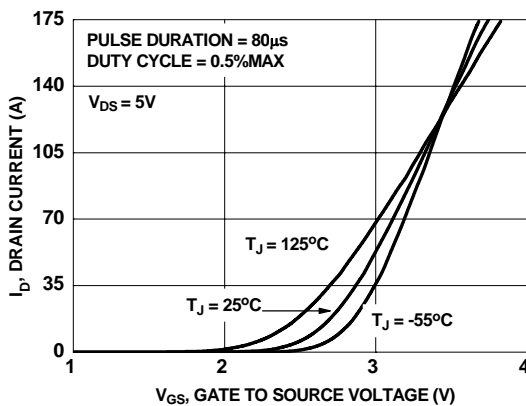


Figure 5. Transfer Characteristics

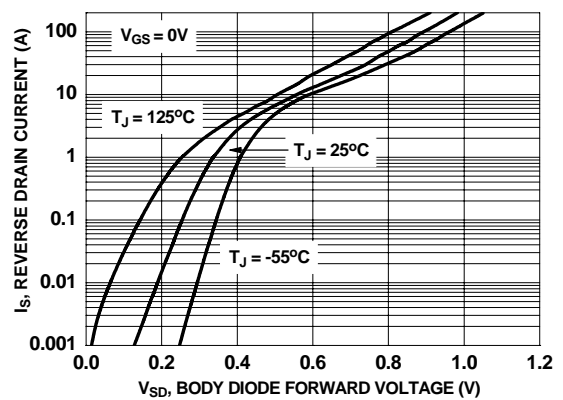
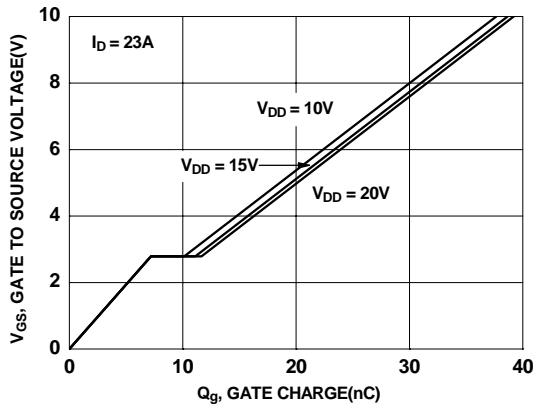
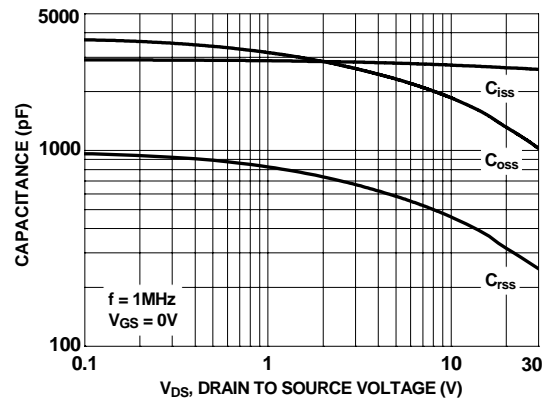


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

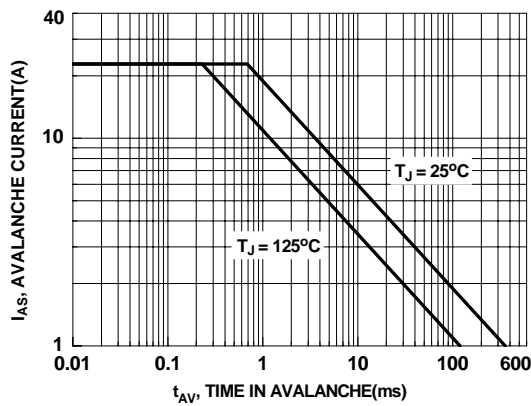
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



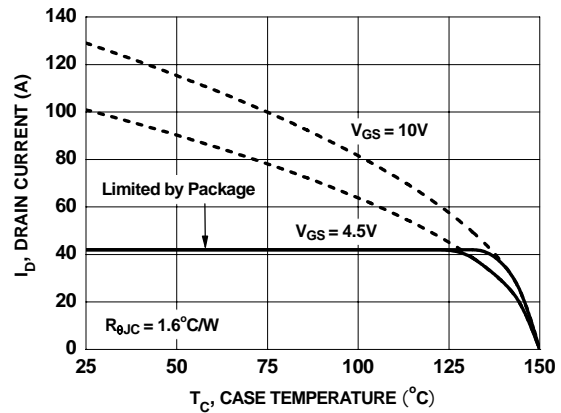
**Figure 7. Gate Charge Characteristics**



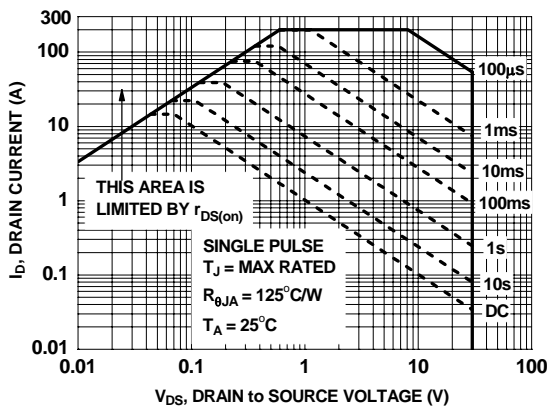
**Figure 8. Capacitance vs Drain to Source Voltage**



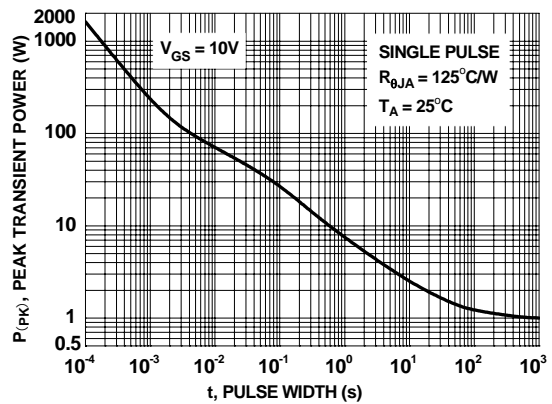
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

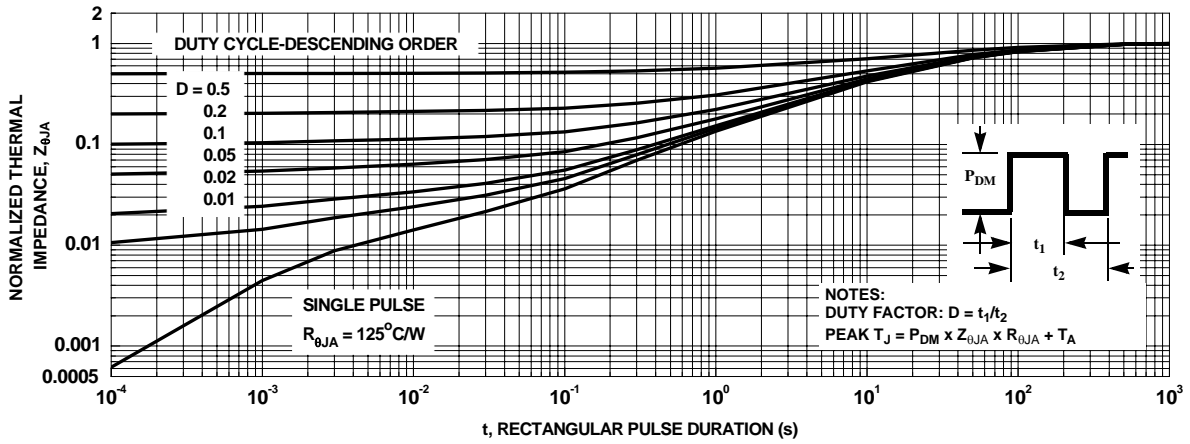


**Figure 11. Forward Bias Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 13. Transient Thermal Response Curve**

## Typical Characteristics (continued)

### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS8670AS.

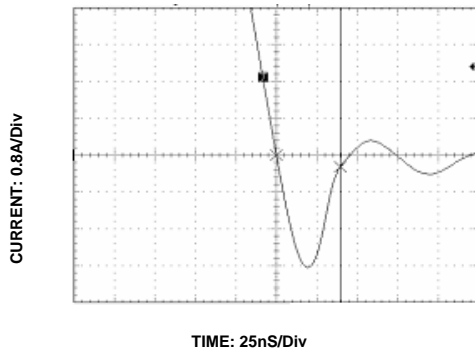


Figure 14. FDMS8670AS SyncFET Body Diode Reverse Recovery Characteristics

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

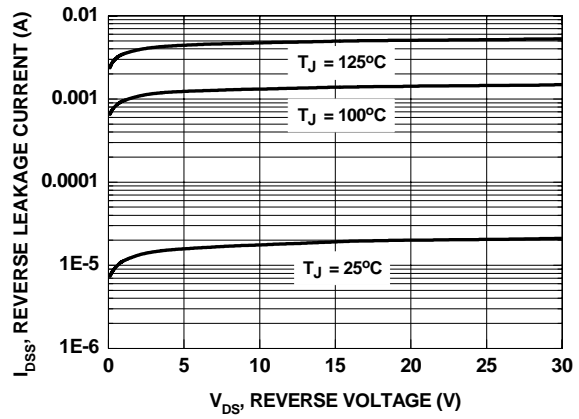



Figure 15. SyncFET Body Diode Reverse Leakage vs Drain to Source Voltage



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